

Peak gate current ($t_p=20\mu s$, $T_j=125$)	I_{GM}	10	A
Average gate power dissipation ($T_j=125$)	$P_{G(AV)}$	1	W
Peak gate power	P_{GM}	20	W
Peak pulse voltage ($T_j=25$; non-repetitive,off-state;FIG.7)	V_{pp}	0.5	kV

($T_j=25$ unless otherwise specified)

Symbol	Test Condition	Value	Unit
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FIG.1: Maximum power dissipation versus RMS on-state current

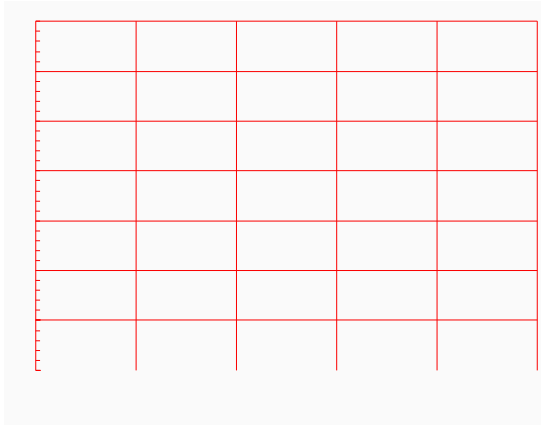
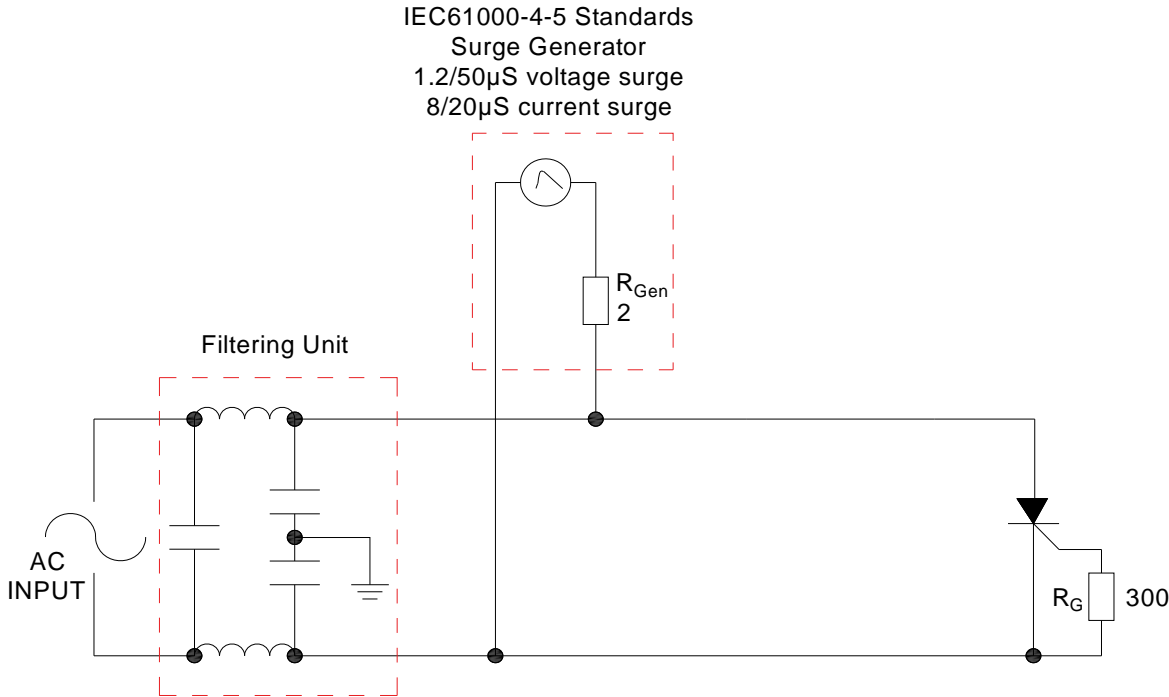
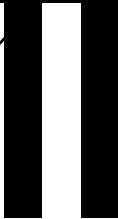
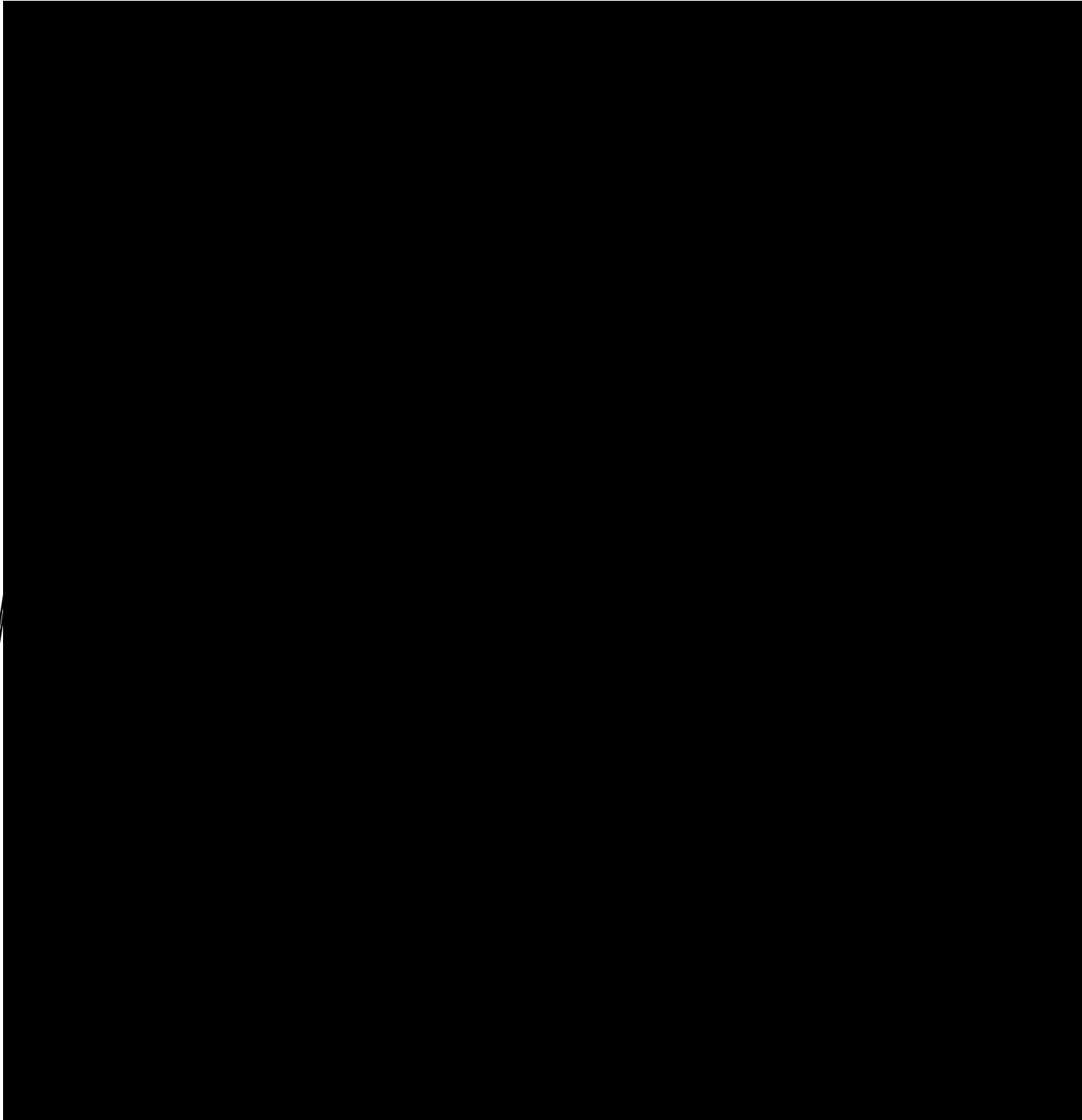


FIG.2: RMS on-state current versus case temperature


FIG.7 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards.



Refer to the application note "Assembly Instructions for Thyristors in Through-hole Package" released by JieJie Microelectronics



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